Prof. ŞEMSETTİN ALTINDAL

Personal Information

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International Researcher IDs

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Education Information

Doctorate, Gazi University, Fen Bilimleri Enstitüsü, Fizik (Dr), Turkey 1986 - 1994
Postgraduate, Gazi University, Fen Bilimleri Enstitüsü, Fizik (Yl) (Tezli), Turkey 1983 - 1985
Undergraduate, Firat University, Faculty Of Scıence, Department Of Physıcs, Turkey 1978 - 1982

Dissertations

Doctorate, Al-siox-psi aygıtların ve güneş pillerinin elektriksel karakteristikleri, Gazi University, Fen Bilimleri Enstitüsü, Fizik (Dr), 1993
Postgraduate, Çok ince yapı teorisi, Gazi University, Fen Bilimleri Enstitüsü, Fizik (Yl) (Tezli), 1950

Research Areas

Semiconductor and Superconductor Materials, Optical Properties, Composites, Nanomaterials, Condensed Matter 1: Structural, Mechanical and Thermal Properties, Intensive Article 2: Electronic Structure, Electric, Magnetic and Optical Properties

Academic Titles / Tasks

Professor, Gazi University, Fen Fakültesi, Fizik, 2011 - Continues
Associate Professor, Gazi University, Fen Fakültesi, Fizik, 2005 - 2011
Assistant Professor, Gazi University, Fen Fakültesi, Fizik, 1994 - 2005
Research Assistant, Gazi University, Fen Fakültesi, Fizik, 1983 - 1994

Advising Theses

ALTINDAL Ş., Photovoltaic and temperature Characteristics of the designed Schottky barrier diodes (SBDs) as a function of temperature and illumination, Doctorate, H.MELOUD(Student), 2021
ALTINDAL Ş., Au/(nanografit-PVP)/n-Si (MPS) yapıların hazırlanması ve elektrik ile dielektrik özelliklerinin geniş bir

frekans ve voltaj aralığında incelenmesi, Doctorate, A.MUHAMMED(Student), 2021

Altındal Ş., DDESIGN, FABRICATION AND CHARACTERIZATION OF A DIELECTRIC MULTILAYER BROADBAND INFRARED METAMATERIAL ABSORBER, Doctorate, B.AKIN(Student), 2021

ALTINDAL Ş., Au/(Ag-ZnO/PVP)/n-Si (MPS) Schottky engel diyotların hazırlanması ve elektrik ile dielektrik özelliklerinin frekans ve voltaja bağlı incelenmesi, Doctorate, Ö.SEVGİLİ(Student), 2020

ALTINDAL Ş., The Fabrıcatıon Of Au/(Ag-Zno/Pvp)/N-Si (Mps) Schottky Barrıer Dıodes And The Investıgatıon Theır Electrıcal And Dıelectrıcal Propertıes As Functıon Of Frequency And Voltage, Doctorate, Ö.SEVGİLİ(Student), 2020

ALTINDAL Ş., Grafen katkılı p-tipi ve n-tipi termoelektrik nanokompozit malzeme üretimi ve karakterizasyonu, Postgraduate, S.KOÇYİĞİT(Student), 2017

ALTINDAL Ş., USLU İ., Productıon And Characterızatıon Of Graphene Doped P-Type And N-Type Thermoelectrıc Nanocomposıte Materıal, Postgraduate, S.KOÇYİĞİT(Student), 2017

ALTINDAL Ş., Polimer arayüzey tabakalı ve tabakasız schottky engel diyotların elektriksel karakteristiklerinin karşılaştırılması, Doctorate, Ç.BİLKAN(Student), 2016

ALTINDAL Ş., The Comparıson Of Electrıcal Characterıstıcs Of Schottky Barrıer Dıodes Wıth And Wıthout Polymer Interfacıal Layer, Doctorate, Ç.BİLKAN(Student), 2016

ALTINDAL Ş., Au/n-GaAs Schottky diyotların hazırlanması ve akım-iletim mekanizmalarının geniş bir sıcaklık aralığında incelenmesi, Doctorate, E.ÖZAVCI(Student), 2015

ALTINDAL Ş., Forward And Reverse Bias Current-Voltage (I-V) Characteristics Of Au/Ca3Co4Ga0,001Ox/n-Si Structures In Temperature Range Of 80-340 K, Doctorate, E.MARIL(Student), 2015

ALTINDAL Ş., Zirkonyum oksit ve gadolinyum oksit tabanlı çeşitli metal oksit katkılı inorganik pigmentlerin çöz-pel tekniğiyle sentezi ve karakterizasyonu, Postgraduate, A.AYTİMUR(Student), 2015

ALTINDAL Ş., USLU İ., Zirkonyum oksit ve gadolinyum oksit tabanlı çeşitli metal oksit katkılı inorganik pigmentlerin çöz-pel tekniğiyle sentezi ve karakterizasyonu, Postgraduate, A.AYTİMUR(Student), 2015

ALTINDAL Ş., Au/ZnO/n-GaAs (MIS) Schottky engel diyotlarin (SBDs) elektriksel karakteristiklerinin frekans ve voltaja bağli incelenmesi, Postgraduate, B.AKIN(Student), 2015

ALTINDAL Ş., Electrıcal And Dıelectrıc Propertıes Of Au/(%1 Graphene (Gp) Doped)-Ca1.9pr0.1co4ox /N-Si Schottky Barrier Dıodes As Functıon Of Temperature And Frequency, Doctorate, H.Gökçen(Student), 2015

ALTINDAL Ş., The Investigatıon Of Frequency And Voltage Dependence Of Main Electrical Parametres Of Au/Zno/N-Gaas (Mıs) Schottky Barrier Diodes (Sbds), Postgraduate, B.AKIN(Student), 2015

ALTINDAL Ş., USLU İ., The Fabrication And Characterization Of Polyvinylidene Fluoride Nanocomposite Piezomaterials Doped Graphene, Boron And Rare Earth Elements, Postgraduate, Y.BADALİ(Student), 2015

ALTINDAL Ş., The Fabrication Of Au/N-Gaas Schottky Diodes And The Investigatıon Of Their Current-Cunduction Mechanisms In Wide Temperature Range, Doctorate, E.ÖZAVCI(Student), 2015

ALTINDAL Ş., Grafen, bor ve nadir toprak elementleriyle katkılanmış polivinililiden florür nanokompozit piezo malzemelerin üretimi ve karakterizasyonu, Postgraduate, Y.BADALİ(Student), 2015

ALTINDAL Ş., Au/(%1 grafen (GP) katkılı)-Ca1.9Pr0.1Co4Ox/n-Si Schottky engel diyotların hazırlanması ve elektrik ile dielektrik özelliklerinin sıcaklık ve frekansa bağlı incelenmesi, Doctorate, H.GÖKÇEN(Student), 2015

ALTINDAL Ş., Au/Ca3Co4Ga0,001Ox/n-Si yapılarda doğru ve ters beslem akım-voltaj (I-V) karakteristiklerinin 80-340 K sıcaklık aralığında incelenmesi, Doctorate, E.MARIL(Student), 2015

ALTINDAL Ş., Au/(%1 grafen (GP) katkılı)-Ca1.9Pr0.1Co4Ox/n-Si Schottky engel diyotların hazırlanması ve elektrik ile dielektrik özelliklerinin sıcaklık ve frekansa bağlı incelenmesi, Doctorate, H.GÖKÇEN(Student), 2015

ALTINDAL Ş., Au/(Zn-Katkılı) polivinil alkol/n-GaAs yapıların hazırlanması ve akım-iletim mekanizmalarının geniş bir sıcaklık aralığında incelenmesi, Doctorate, H.TECİMER(Student), 2014

ALTINDAL Ş., The Preperation Of Au/Pva:Zn/N-Si (Mps) Structures And Investigation Of Main Electrical Characteristics Under Illumination, Doctorate, U.AYDEMİR(Student), 2014

ALTINDAL Ş., Au/PVA:Zn/n-Si (MPS) yapıların hazırlanması ve temel elektriksel özelliklerinin ışık altında incelenmesi, Doctorate, U.AYDEMİR(Student), 2014

ALTINDAL Ş., The preparation of Au/(Zn-Doped) polyvinyl alcohol/n-GaAs structures and the investigation of their current-transport mechanisms in the wide temperature, Doctorate, H.TECİMER(Student), 2014

ALTINDAL Ş., The preparation of Au/n-4H-SIC (MS) schottky diodes and the investigation their electrical characteristicsas function of frequency, Postgraduate, Ö.SEVGİLİ(Student), 2013

ALTINDAL Ş., Metal-polimer-yarıiletken (MPS) yapıların elektrik ve dielektrik özelliklerinin geniş frekans aralığında incelenmesi, Doctorate, A.KAYA(Student), 2013

ALTINDAL Ş., A comparative study on the electrical characterization of Al/p-Si (MS) structures with and without interfacial perylene (C20H12) layer at room temperature, Postgraduate, Ç.BİLKAN(Student), 2013

ALTINDAL Ş., Au/n-4H-SiC (MS) schottky diyotların hazırlanması ve elektriksel karekteristiklerinin frekansa bağlı incelenmesi, Postgraduate, Ö.SEVGİLİ(Student), 2013

ALTINDAL Ş., The investigation of electrical and dielectric properties of metal-polymer-semiconductor (MPS) structures in the wide frequency range, Doctorate, A.KAYA(Student), 2013

ALTINDAL Ş., Perilensiz ve perilenli Al/p-Si schottky engel diyotların elektriksel özelliklerinin oda sıcaklığında karşılaştırılması, Postgraduate, Ç.BİLKAN(Student), 2013

ALTINDAL Ş., (Ni/Au)/Al0. 22Ga0. 78N/AlN/GaN çoklu-yapıların elektriksel karakteristiklerinin admitans spektroskopi metoduyla incelenmesi, Doctorate, Y.ŞAFAK(Student), 2012

ALTINDAL Ş., The investigation of temperature and radiation dependent electrical characteristics of au/pva:zn/n-si (mps) schottky barrier diodes, Doctorate, İ.TAŞÇIOĞLU(Student), 2012

ALTINDAL Ş., Metal-yalıtkan-yarıiletken (Al/SiO2/p-Si) yapıların elektrik ve dielektrik özelliklerinin frekans ve potansiyele bağlı incelenmesi, Doctorate, Z.SÖNMEZ(Student), 2012

ALTINDAL Ş., Metal-yalıtkan-yarıiletken (Al/SiO2/p-Si) yapıların elektrik ve dielektrik özelliklerinin frekans ve potansiyele bağlı incelenmesi, Doctorate, Z.SÖNMEZ(Student), 2012

ALTINDAL Ş., The investigation of electrical properties of (Ni/Au)/Al0.22Ga0.78N/AlN/GaN hetero-structures by using admittance spectroscopy method, Doctorate, Y.ŞAFAK(Student), 2012

ALTINDAL Ş., Au/PVA:Zn/n-Si (MPS)schottky engel diyodun elektriksel özelliklerinin sıcaklık ve radyasyona bağlı incelenmesi, Doctorate, İ.TAŞÇIOĞLU(Student), 2012

ALTINDAL Ş., The ınvestıgatıon of temperature dependent electrıc and dıelectrıc characterıstıcs of Au/SiO2/n-Si (MIS) structure, Postgraduate, A.GÜL(Student), 2011

ALTINDAL Ş., Al / Rhodamine - 101 / n-GaAs Schottky Engel diyotlarının hazırlanması ve iletim mekanizmalarının geniş bir sıcaklık aralığında incelenmesi, Doctorate, Ö.VURAL(Student), 2011

ALTINDAL Ş., Au/SİO2/n-Sİ (MIS) yapının elektrik ve dielektrik karakteristiklerinin sıcaklığa bağlı incelenmesi, Postgraduate, A.GÜL(Student), 2011

ALTINDAL Ş., The preparatinon of al/rhodamine-101/n-gaas schottky barrier diodes and the investigation of their cundiction mechanisms in the wide temperature range, Doctorate, Ö.VURAL(Student), 2011

ALTINDAL Ş., Au/(Bi-katkılı) polivinil alkol/n-si schottky engel diyotlarının elektriksel özelliklerinin sıcaklığa ve aydınlatma şiddetıne bağlı incelenmesi, Postgraduate, H.GÖKÇEN(Student), 2011

ALTINDAL Ş., Au/(Bi-katkılı) polivinil alkol/n-si schottky engel diyotlarının elektriksel özelliklerinin sıcaklığa ve aydınlatma şiddetıne bağlı incelenmesi, Postgraduate, H.GÖKÇEN(Student), 2011

ALTINDAL Ş., Al/SiO2/p-Si (MIS) yapıların elektrik karekteristiklerinin frekansa bağlı incelenmesi, Postgraduate, A.KAYA(Student), 2010

ALTINDAL Ş., Al/SiO2/p-Si (MIS) yapıların elektrik karekteristiklerinin frekansa bağlı incelenmesi, Postgraduate, A.KAYA(Student), 2010

ALTINDAL Ş., The preparation of Au/polyvinyl alcohol (Co, Zn-doped)/n-Si schottky barrier diodes and the investigation of their electrical characteristics as a function of illumination intensity, Doctorate, H.USLU(Student), 2010

ALTINDAL Ş., NiAu-AlGaN/GaN heteroyapıların elektriksel karakteristiklerinin sıcaklığa bağlı incelenmesi, Doctorate, S.DEMİREZEN(Student), 2010

ALTINDAL Ş., NiAu-AlGaN/GaN heteroyapıların elektriksel karakteristiklerinin sıcaklığa bağlı incelenmesi, Doctorate, S.DEMİREZEN(Student), 2010

ALTINDAL Ş., SiO2/p-Si (MIS) YAPILARIN ELEKTRİK KARAKTERİSTİKLERİNİN FREKANSA BAĞLI İNCELENMESİ, Postgraduate, A.KAYA(Student), 2010

ALTINDAL Ş., NiAu-AlGaN/GaN HETEROYAPILARIN ELEKTRİKSEL KARAKTERİSTİKLERİNİN SICAKLIĞA BAĞLI İNCELENMESİ, Doctorate, S.DEMİREZEN(Student), 2010

ALTINDAL Ş., Au/(Co, Zn-katkılı) polivinil alkol/n-Si schottky engel diyotlarının hazırlanması ve elektriksel özelliklerinin aydınlatma şiddetine bağlı incelenmesi, Doctorate, H.USLU(Student), 2010

ALTINDAL Ş., Au/SrTiO3/n-Si (MFS) Schottky diyotların elektriksel parametrelerinin I-V, C-V ve DLTS metodu ile incelenmesi, Postgraduate, U.AYDEMİR(Student), 2009

ALTINDAL Ş., THE INVESTIGATION OF FREQUENCY DEPENDENT ELECTRICAL CHARACTERIZATION OF Au/SrTiO3/n-Si (MFS) SCHOTTKY DIODES, Postgraduate, U.AYDEMİR(Student), 2009

ALTINDAL Ş., Yalıtkan tabakalı Al/p-Si Schottky diyotlarda elektriksel karakteristiklerin sıcaklığa bağlı incelenmesi, Doctorate, H.KANBUR(Student), 2008

ALTINDAL Ş., THE INVESTIGETION OF FREQUENCY AND TEMPERATURE DEPENDENCE OF ELECTRICAL AND DIELECTRIC PROPERTIES OF Au/SiO2/n-GaAs (MOS) STRUCTURES, Doctorate, M.GÖKÇEN(Student), 2008

ALTINDAL Ş., THE INVESTIGATION OF TEMPERATURE DEPENDENCE CURRENT-CONDUCTION MECHANISM AND ELECTRICAL CHARACTERISTICS OF Al/SiO2/p-Si (MIS) STUCTURES, Doctorate, D.Esra(Student), 2008

ALTINDAL Ş., THE INVESTIGATION OF TEMPERATURE DEPENDENCE OF ELECTRICAL CHARACTERISTICS OF THE Al/p-Si SCHOTTKY DIODES WITH INSULATOR LAYER, Doctorate, H.KANBUR(Student), 2008

ALTINDAL Ş., Al/SiO2/p-Si (MYY) yapıların akım iletim mekanizması ve elektriksel özelliklerinin sıcaklığa bağlı incelenmesi, Doctorate, D.ESRA(Student), 2008

ALTINDAL Ş., Au/SiO2/n-GaAs (MOY) yapıların elektrik ve dielektrik karakteristiklerinin frekans ve sıcaklığa bağlı incelenmesi, Doctorate, M.GÖKÇEN(Student), 2008

ALTINDAL Ş., Au/SiO2/n-GaAs (MOY) yapıların elektrik ve dielektrik karakteristiklerinin frekans ve sıcaklığa bağlı incelenmesi, Doctorate, M.GÖKÇEN(Student), 2008

ALTINDAL Ş., Al/SiO2/p-Si (MYY) yapıların akım iletim mekanizması ve elektriksel özelliklerinin sıcaklığa bağlı incelenmesi, Doctorate, D.ESRA(Student), 2008

ALTINDAL Ş., Au/Bi4Ti3O12/SiO2/n-Si yapıların hazırlanması, elektriksel ve dielektrik özelliklerinin frekans ve sıcaklığa bağlı incelenmesi, Doctorate, F.PARLAKTÜRK(Student), 2007

ALTINDAL Ş., Au/Bi4Ti3O12/SiO2/n-Si yapıların hazırlanması, elektriksel ve dielektrik özelliklerinin frekans ve sıcaklığa bağlı incelenmesi, Doctorate, F.PARLAKTÜRK(Student), 2007

ALTINDAL Ş., THE INVESTIGATION OF TEMPERATURE DEPENDENT ELECTRICAL CHARACTERISTICS OF SCHOTTKY DIODES, Postgraduate, H.KUTLUCA(Student), 2007

ALTINDAL Ş., Schottky diyotların elektriksel karakteristiklerinin sıcaklığa bağlı incelenmesi, Postgraduate, H.KUTLUCA(Student), 2007

ALTINDAL Ş., THE PREPARATION OF Au/Bi4Ti3O12/SiO2/n-Si STRUCTURES, INVESTIGATION OF THE ELECTRICAL AND DIELECTRIC PROPERTIES BASED ON FREQUENCY AND TEMPERATURE, Doctorate, F.PARLAKTÜRK(Student), 2007

ALTINDAL Ş., (Al-TiW+PtSi)/n-Si Schottky diyotların elektriksel özelliklerinin frekans ve aydınlanma şiddetine bağlı incelenmesi, Postgraduate, M.HAMDİ(Student), 2007

ALTINDAL Ş., INVESTIGATION OF ELECTRICAL CHARACTERISTICS OF (Al-TiW+PtSi)-n-Si SCHOTTKY DIODES DEPENDING ON FREQUENCY AND ILLUMINATION, Postgraduate, M.HAMDİ(Student), 2007

ALTINDAL Ş., Schottky diyotların elektriksel karakteristiklerinin sıcaklığa bağlı incelenmesi, Postgraduate, H.KUTLUCA(Student), 2007

ALTINDAL Ş., Metal-yalıtkan-yarı iletken (MIS) yapılarda elektrik ve dielektrik özelliklerinin sıcaklık ve frekansa bağlı incelenmesi, Doctorate, İ.YÜCEDAĞ(Student), 2007

ALTINDAL Ş., Metal-yalıtkan-yarı iletken (MIS) yapılarda elektrik ve dielektrik özelliklerinin sıcaklık ve frekansa bağlı incelenmesi, Doctorate, İ.YÜCEDAĞ(Student), 2007

ALTINDAL Ş., MIS yapıların frekans ve radyasyona bağlı temel elektriksel parametreleri, Postgraduate, B.TATAROĞLU(Student), 2006

ALTINDAL Ş., MIS yapıların frekans ve radyasyona bağlı temel elektriksel parametreleri, Postgraduate, B.TATAROĞLU(Student), 2006

ALTINDAL Ş., Doğal yalıtkan tabakalı Al/p-Si Schottky diyotlarda elektriksel karakteristiklerin frekansa bağlı incelenmesi, Postgraduate, H.KANBUR(Student), 2005

ALTINDAL Ş., Doğal yalıtkan tabakalı Al/p-Si schottky diyotlarda elektriksel karakteristiklerin frekansa bağlı incelenmesi, Postgraduate, H.KAMBUR(Student), 2005

ALTINDAL Ş., Doğal yalıtkan tabakalı Al/p-Si schottky diyotlarda elektriksel karakteristiklerin frekansa bağlı incelenmesi, Postgraduate, H.KAMBUR(Student), 2005

ALTINDAL Ş., (Al-TiW+PtSi)/n-Si Sckottky diyotlarının sıcaklığa bağlı temel parametreleri, Postgraduate, E.MARIL(Student), 2005

ALTINDAL Ş., (Al-TiW+PtSi)/n-Si Sckottky diyotlarının sıcaklığa bağlı temel parametreleri, Postgraduate, E.MARIL(Student), 2005

ALTINDAL Ş., Doğal yalıtkan tabakalı Al/p-Si Schottky diyotlarda elektriksel karakteristiklerin frekansa bağlı incelenmesi, Postgraduate, H.KANBUR(Student), 2005

ALTINDAL Ş., MOS yapılarda temel fiziksel parametrelerin frekans ve radyasyon miktarına bağlı incelenmesi, Doctorate, A.TATAROĞLU(Student), 2004

ALTINDAL Ş., MOS yapılarda temel fiziksel parametrelerin frekans ve radyasyon miktarına bağlı incelenmesi, Doctorate, A.TATAROĞLU(Student), 2004

ALTINDAL Ş., MOS yapılarda kapasitans-voltaj (C-V) ve iletkenlik voltaj (G/W-V) karakteristiklerinin frekans ve radyasyona bağlı incelenmesi, Postgraduate, M.GÖKÇEN(Student), 2003

ALTINDAL Ş., MOS yapılarda kapasitans-voltaj (C-V) ve iletkenlik voltaj (G/W-V) karakteristiklerinin frekans ve radyasyona bağlı incelenmesi, Postgraduate, M.GÖKÇEN(Student), 2003

ALTINDAL Ş., Yalıtkan arayüzey tabakası ve seri dirence sahip Al/ SnO2/ p-Si schottky diyotların elektriksel karakteristiklerinin sıcaklığa bağlı incelenmesi, Postgraduate, Z.TEKELİ(Student), 2002

ALTINDAL Ş., Al/p-Si ve Au/n-Si schottky diyotlarda I-V ve C-V karakteristiklerinin geniş bir sıcaklık aralığında analizi, Doctorate, İ.DÖKME(Student), 2002

ALTINDAL Ş., Yalıtkan arayüzey tabakası ve seri dirence sahip Al/ SnO2/ p-Si schottky diyotların elektriksel karakteristiklerinin sıcaklığa bağlı incelenmesi, Postgraduate, Z.TEKELİ(Student), 2002

ALTINDAL Ş., Al/p-Si ve Au/n-Si schottky diyotlarda I-V ve C-V karakteristiklerinin geniş bir sıcaklık aralığında analizi, Doctorate, İ.DÖKME(Student), 2002

ALTINDAL Ş., Güneş pillerinde arayüzey durumlarının c.v. karakteristiklerine etkisi, Postgraduate, E.YILDIZ(Student), 1999

ALTINDAL Ş., Güneş pillerinde arayüzey durumlarının c.v. karakteristiklerine etkisi, Postgraduate, E.YILDIZ(Student), 1999

ALTINDAL Ş., Metal-oksit-yarıiletken (MOS) kapasitörlerde dielektrik sabitinin frekans, sıcaklık ve kalınlığa bağlı incelenmesi, Postgraduate, A.TATAROĞLU(Student), 1999

ALTINDAL Ş., Metal-oksit-yarıiletken (MOS) kapasitörlerde dielektrik sabitinin frekans, sıcaklık ve kalınlığa bağlı incelenmesi, Postgraduate, A.TATAROĞLU(Student), 1999

ALTINDAL Ş., Arayüz oksit tabakası ve seri dirence sahip ruln-Si schottky diyod parametrelerinin doğru beslem I-V ve C-V karakteristiklerinden hesaplanması, Postgraduate, Ö.VURAL(Student), 1998

ALTINDAL Ş., Arayüz oksit tabakası ve seri dirence sahip ruln-Si schottky diyod parametrelerinin doğru beslem I-V ve C-V karakteristiklerinden hesaplanması, Postgraduate, Ö.VURAL(Student), 1998

ALTINDAL Ş., AI-SiO2-pSİ (MYY) güneş pillerinin sıcaklığa bağlı elektriksel karakteristikleri, Postgraduate, C.TEMEL(Student), 1997

ALTINDAL Ş., AI-SiO2-pSİ (MYY) güneş pillerinin sıcaklığa bağlı elektriksel karakteristikleri, Postgraduate, C.TEMEL(Student), 1997

Published journal articles indexed by SCI, SSCI, and AHCI

I. **On a detail examination of frequency and voltage dependence of dielectric, electric modulus, ac conductivity (σac) of the Al/DLC/p-Si structures between 2 kHz and 1 MHz**
BALCI E., Vahid A. F., Avar B., ALTINDAL Ş.
Physica B: Condensed Matter, vol.695, 2024 (SCI-Expanded)

II. **Quaternary functional semiconductor device-based temperature sensors for low and high temperatures (LTs, HTs)**
ALTINDAL Ş., Yildiz K., Dere A., Orman Y., Yakuphanoglu F.
PHYSICA SCRIPTA, vol.99, no.12, 2024 (SCI-Expanded)

III. **The current–voltage (I–V) characteristics and low–high impedance measurements (C/G–V) of Au/(AgCdS:PVP)/n-Si Schottky diode (SD) at dark and under illumination conditions**
Aslanbaş G., DURMUŞ P., ALTINDAL Ş., AZIZIAN-KALANDARAGH Y.

Journal of Materials Science: Materials in Electronics, vol.35, no.36, 2024 (SCI-Expanded)

IV. **A high sensitivity temperature coefficient of the Au/n-Si with (CdTe-PVA) structure based on capacitance/conductance-voltage (C/G-V) measurements in a wide range of temperature**
ERBİLEN TANRIKULU E., Güçlü Ç. Ş., ALTINDAL Ş., Durmuş H.
Measurement: Journal of the International Measurement Confederation, vol.238, 2024 (SCI-Expanded)

V. **A comparative study of the Au/n-Si (MS) and Au/(ZnO:CeO2:PVP)/n-Si (MPS) Schottky structures by using current/voltage characteristics in dark and under illumination**
Üstün O., ÖZÇELİK U., AZIZIAN-KALANDARAGH Y., ALTINDAL Ş., ÖZÇELİK S.
Physica Scripta, vol.99, no.9, 2024 (SCI-Expanded)

VI. **Overview of the irradiation-dependent behaviour of the negative dielectric properties of GaAs-based MIS devices**
EVCİN BAYDİLLİ E., Kaymaz A., ALTINDAL Ş.
Radiation Physics and Chemistry, vol.222, 2024 (SCI-Expanded)

VII. **Examination of Electrical and Dielectric Parameters of Au/n-Si Schottky Barrier Diodes (SBDs) with Organic Perylene Interlayer Using Impedance Measurements Under Various Illumination Intensities**
Bengi S., ÇETİNKAYA H. G., ALTINDAL Ş., Zeyrek S.
Journal of Electronic Materials, vol.53, no.9, pp.5606-5616, 2024 (SCI-Expanded)

VIII. **Machine learning-assisted prediction of the electronic features of a Schottky diode interlaid with PVP:BaTiO3 composite**
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Non Academic Experience

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